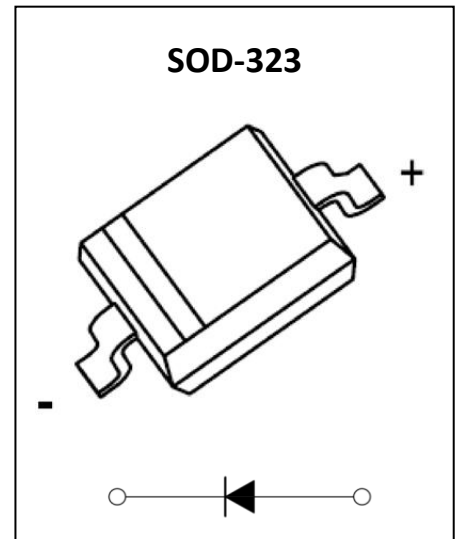


GP5817WS Schottky Barrier Diode
Feature

- Small power mold type
- Low VF
- Low IR
- High reliability

Application

- High frequency inverters
- Free wheeling
- Polarity protection applications


MARKING:

ABSOLUTE MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

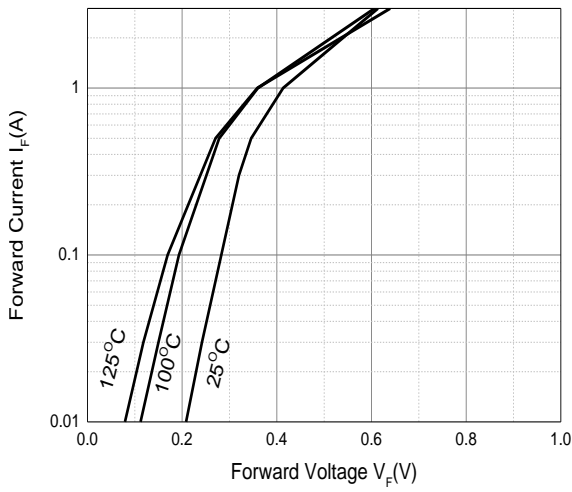
Parameter	Symbol	Value	Unit
DC reverse voltage	V _R	20	V
Mean rectifying current	I _o	1	A
Non-repetitive Peak Forward Surge Current @ t=8.3ms	I _{FSM}	15	A
IEC 61000-4-2 ESD Voltage Air Model	V _{ESD}	±15	KV
IEC 61000-4-2 ESD Voltage Contact Model		±8	KV
Power Dissipation	P _D	0.25	W
Thermal Resistance from Junction to Ambient	R _{θJA}	400	°C/W
Junction Temperature	T _J	125	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise noted)

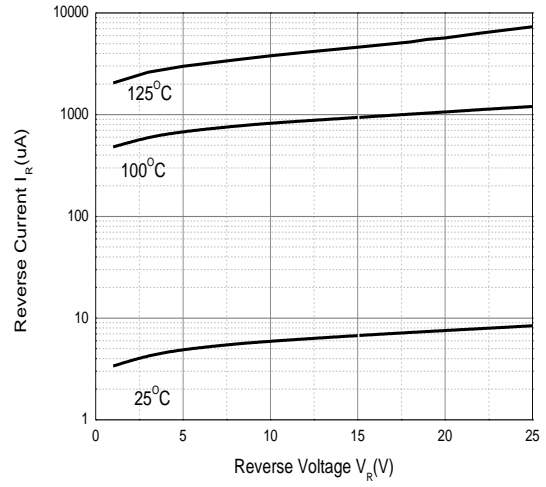
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Reverse voltage	V _{BR}	I _R =250μA	20			V
Forward voltage	V _F	I _F =0.5A	0	0.37	0.40	V
		I _F =1.0A	0	0.42	0.45	V
		I _F =3.0A	0	0.62	0.75	V
Reverse current	I _R	V _R =20V		5	50	μA
Diode capacitance	C _D	V _R =4V, f=1MHz		60		pF

Typical Electrical and Thermal Characteristics

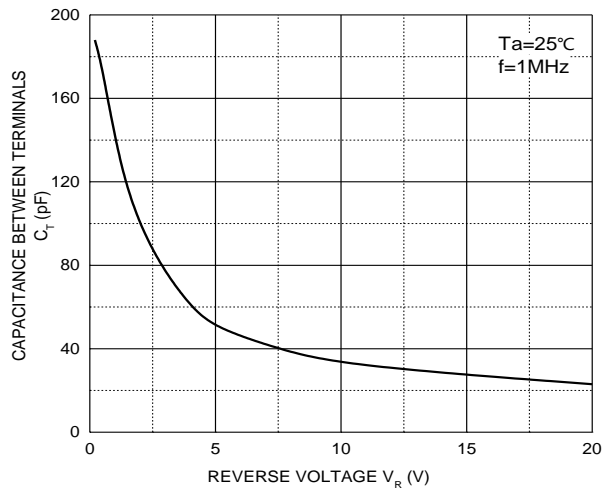
Forward Characteristics



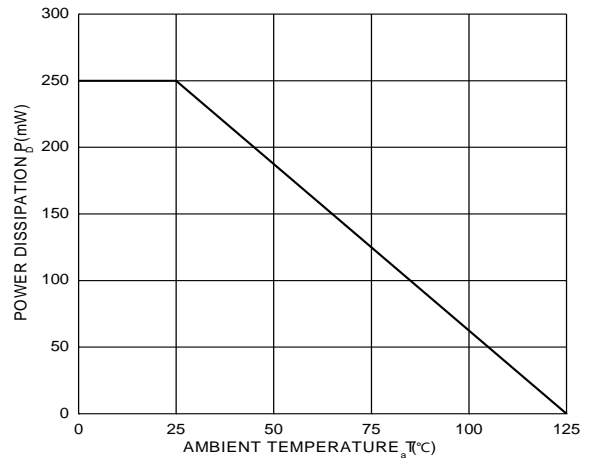
Reverse Characteristics

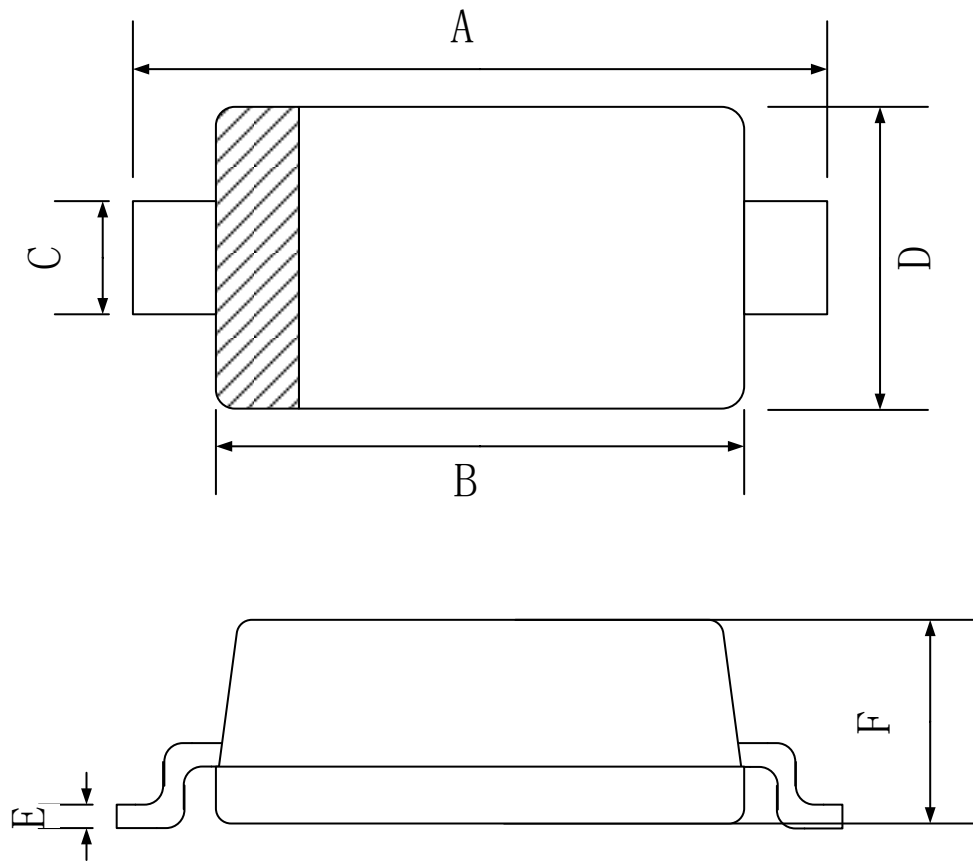


Capacitance Characteristics



Power Derating Curve



SOD-323 Package Outline Dimensions


Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	2.30	2.50	2.70
B	1.60	1.70	1.90
C	0.25	0.325	0.40
D	1.15	1.25	1.35
E	0.089	0.095	0.101
F	0.80	0.90	1.00